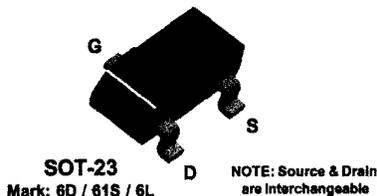
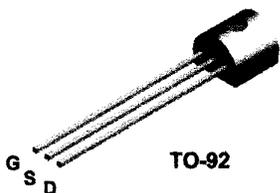


2N5457
2N5458
2N5459

MMBF5457
MMBF5458
MMBF5459



2N5457 / 5458 / 5459 / MMBF5457 / 5458 / 5459

N-Channel General Purpose Amplifier

This device is a low level audio amplifier and switching transistors, and can be used for analog switching applications. Sourced from Process 55.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	25	V
V_{GS}	Gate-Source Voltage	- 25	V
I_{GF}	Forward Gate Current	10	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5457-5459	*MMBF5457-5459	
P_D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

N-Channel General Purpose Amplifier

(continued)

2N5457 / 5458 / 5459 / MMBF5457 / 5458 / 5459

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$I_G = 10 \mu A, V_{DS} = 0$	-25			V
I_{GSS}	Gate Reverse Current	$V_{GS} = -15 V, V_{DS} = 0$ $V_{GS} = -15 V, V_{DS} = 0, T_A = 100^\circ C$			-1.0 -200	nA nA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	$V_{DS} = 15 V, I_D = 10 nA$	-0.5 -1.0 -2.0		-6.0 -7.0 -8.0	V V V
V_{GS}	Gate-Source Voltage	$V_{DS} = 15 V, I_D = 100 \mu A$ $V_{DS} = 15 V, I_D = 200 \mu A$ $V_{DS} = 15 V, I_D = 400 \mu A$		-2.5 -3.5 -4.5		V V V

ON CHARACTERISTICS

I_{DSS}	Zero-Gate Voltage Drain Current*	$V_{DS} = 15 V, V_{GS} = 0$	5457 5458 5459	1.0 2.0 4.0	3.0 6.0 9.0	5.0 9.0 16	mA mA mA
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SMALL SIGNAL CHARACTERISTICS

g_{fs}	Forward Transfer Conductance*	$V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz$	5457 5458 5459	1000 1500 2000		5000 5500 6000	$\mu mhos$ $\mu mhos$ $\mu mhos$
g_{os}	Output Conductance*	$V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz$			10	50	$\mu mhos$
C_{iss}	Input Capacitance	$V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz$			4.5	7.0	pF
C_{rss}	Reverse Transfer Capacitance	$V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz$			1.5	3.0	pF
NF	Noise Figure	$V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz,$ $R_G = 1.0 megohm, BW = 1.0 Hz$				3.0	dB

*Pulse Test: Pulse Width $\leq 300 ms$, Duty Cycle $\leq 2\%$

Typical Characteristics

